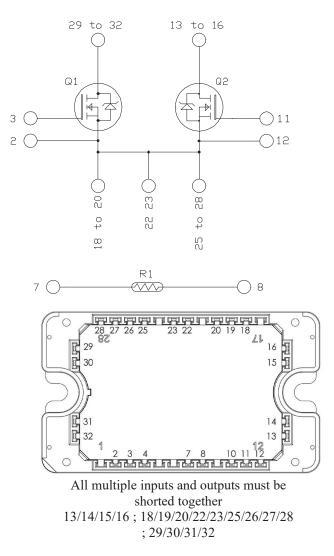
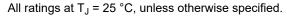


## **Dual Common Source SiC MOSFET Power Module**

#### **Product Overview**

The MSCSM70DUM07T3AG device is a 700V/353A dual common source silicon carbide (SiC) MOSFET power module.





Δ CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

### Features

The following are the key features of MSCSM70DUM07T3AG device:

- SiC Power MOSFET
  - Low R<sub>DS(on)</sub>
  - High temperature performance
  - Kelvin source for easy drive
- Low stray inductance
- High level of integration
- Aluminum Nitride (AIN) substrate for improved thermal performance
- Internal thermistor for temperature monitoring

### **Benefits**

•

The following are the benefits of MSCSM70DUM07T3AG device:

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS compliant
- Solderable terminals both for power and signal for easy PCB mounting

## Application

The following are the applications of MSCSM70DUM07T3AG device:

AC switches

### 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM70DUM07T3AG device.

#### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings of the MSCSM70DUM07T3AG device.

#### Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Parameter		Unit
V <sub>DSS</sub>	Drain-Source voltage	Drain-Source voltage		V
I <sub>D</sub>	Continuous drain current	Continuous drain current $T_{C} = 25 \ ^{\circ}C$		A
	T <sub>C</sub> = 80 °C		281	
I <sub>DM</sub>	Pulsed drain current	Pulsed drain current		
V <sub>GS</sub>	Gate-Source voltage	Gate-Source voltage		V
R <sub>DS(on)</sub>	Drain-Source ON resistance		6.4	mΩ
P <sub>D</sub>	Power dissipation	T <sub>C</sub> = 25 °C	988	W

The following table lists the electrical characteristics of the MSCSM70DUM07T3AG device.

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0V V <sub>DS</sub> = 700V		_		300	μA
R <sub>DS(on)</sub>	Drain–Source on resistance	V <sub>GS</sub> = 20V I <sub>D</sub> = 120A	T <sub>J</sub> = 25 °C T <sub>J</sub> = 175 °C	<u> </u>	5 6.3	6.4 —	mΩ
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 12 \text{ mA}$		1.9	2.4	—	V
I <sub>GSS</sub>	Gate–Source leakage current	V <sub>GS</sub> = 20V V <sub>DS</sub> = 0V				300	nA

#### Table 1-2. Electrical Characteristics

**Electrical Specifications** 

The following table lists the dynamic characteristics of the MSCSM70DUM07T3AG device.

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0V V <sub>DS</sub> = 700V f = 1 MHz		_	13.5	_	nF
Coss	Output capacitance			—	1.5	-	
C <sub>rss</sub>	Reverse transfer capacitance			_	0.09	_	
Qg	Total gate charge	VGS = -5V/20V		_	645	_	nC
Qgs	Gate-Source charge	V <sub>Bus</sub> = 470V		_	174	_	
Q <sub>gd</sub>	Gate-Drain charge	I <sub>D</sub> = 120A		_	105	_	_
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GS</sub> = -5V/20V	Т <sub>Ј</sub> = 150 °С	_	40	_	ns
Tr	Rise time	V <sub>Bus</sub> = 400V		_	35	_	
T <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 240A		_	50	_	_
Τf	Fall time	R <sub>Gon</sub> = 9Ω R <sub>Goff</sub> = 1.6Ω			20	-	
Eon	Turn-on energy	V <sub>GS</sub> = -5V/20V	Т <sub>Ј</sub> = 150 °С	_	1.9	_	mJ
E <sub>off</sub>	Turn-off energy	V <sub>Bus</sub> = 400V I <sub>D</sub> = 240A R <sub>Gon</sub> = 9Ω R <sub>Goff</sub> = 1.6Ω	TJ = 150 °C	-	0.56	-	
RGint	Internal gate resistance			_	1.9	_	Ω
R <sub>th</sub> JC	Junction-to-case thermal resistance			-	-	0.152	°C/W

#### Table 1-3. Dynamic Characteristics

The following table lists the body diode ratings and characteristics of the MSCSM70DUM07T3AG device.

#### Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>SD</sub>	Diode forward voltage	V <sub>GS</sub> = 0V I <sub>SD</sub> = 120A		3.4		V
		V <sub>GS</sub> = -5V I <sub>SD</sub> = 120A	—	3.8	—	
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 120A		38		ns
Q <sub>rr</sub>	Reverse recovery charge	$V_{GS} = -5V$		954		nC
Irr	Reverse recovery current	V <sub>R</sub> = 470V di <sub>F</sub> /dt = 3000A/µs		44		A

#### **Electrical Specifications**

#### 1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM70DUM07T3AG device.

Symbol	Characteristic			Min.	Max.	Unit
V <sub>ISOL</sub>	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			4000	—	V
TJ	Operating junction temperature range	Operating junction temperature range			175	°C
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>Jmax</sub> –25	
T <sub>STG</sub>	Storage case temperature			-40	125	
T <sub>C</sub>	Operating case temperature	Operating case temperature			125	_
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight			_	110	g

#### Table 1-5. Thermal and Package Characteristics

The following table lists the temperature sensor NTC of the MSCSM70DUM07T3AG device.

#### Table 1-6. Temperature Sensor NTC

Symbol	Characteristic		Min.	Тур.	Max.	Unit
R <sub>25</sub>	Resistance at 25 °C		—	50	—	kΩ
$\Delta R_{25}/R_{25}$	-		—	5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15K		_	3952	_	К
ΔΒ/Β	—	T <sub>C</sub> = 100 °C	—	4		%

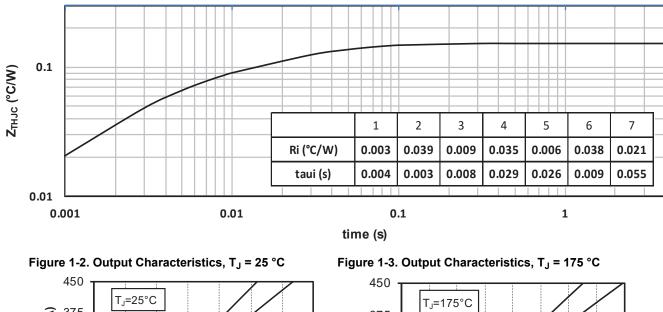
$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature T  
R<sub>T</sub>: Thermistor value at T

**Note:** See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

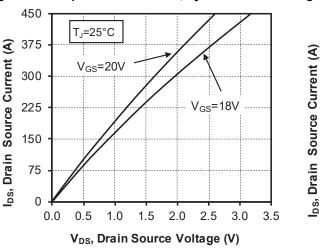
**Electrical Specifications** 

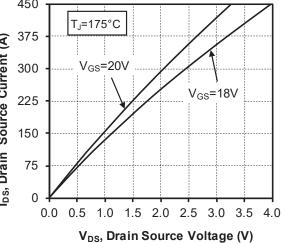
#### 1.3 Typical SiC MOSFET Performance Curve (Per SiC MOSFET)

This section shows the typical SiC MOSFET performance curves of the MSCSM70DUM07T3AG device.

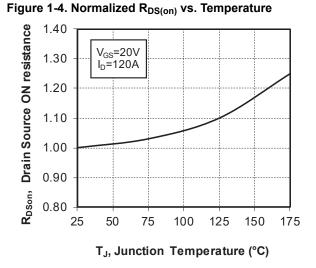


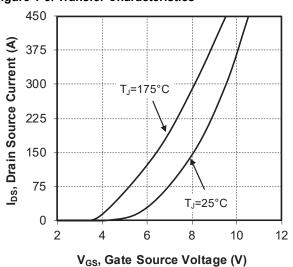
#### Figure 1-1. Junction-to-Heatsink Thermal Impedance

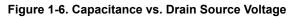


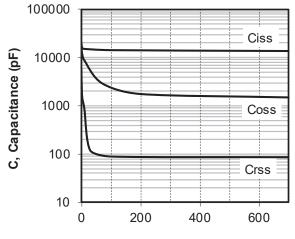


**Electrical Specifications** 









V<sub>DS</sub>, Drain source Voltage (V)



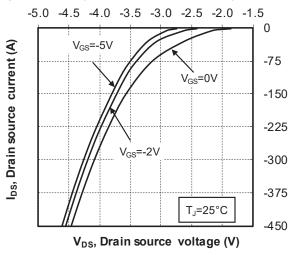
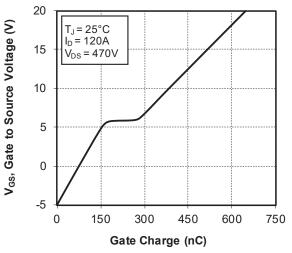
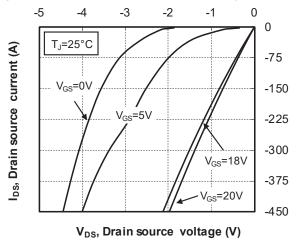


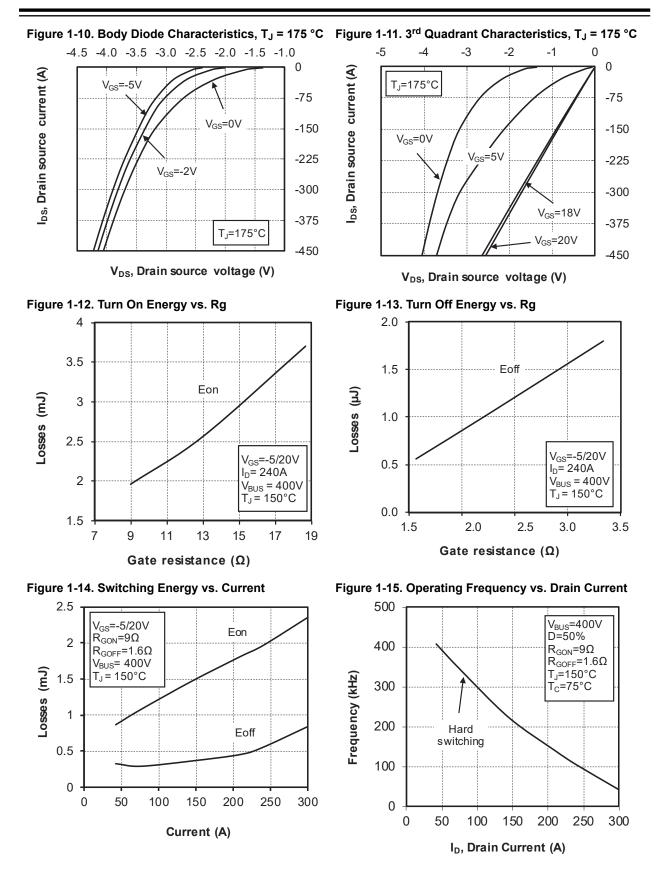
Figure 1-7. Gate Charge vs. Gate Source Voltage







**Electrical Specifications** 



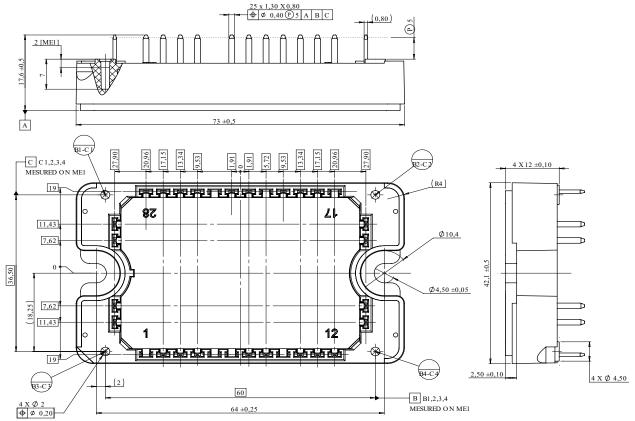
### 2. Package Specifications

The following section shows the package specification of the MSCSM70DUM07T3AG device.

#### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70DUM07T3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



**Note:** See application note AN3500A—Mounting Instructions for SP1F and SP3F Power Modules for more information.

## 3. Revision History

Revision	Date	Description
Α	12/2021	Initial Revision.

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